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Product Data Sheet

UV LED Chip

EOLC-395-34

Rev. 03, 2017

Radiation	Type	Electrodes
ultraviolet (UV)	InGaN / sapphire	P + N up

<p style="text-align: center;">Unit: μm</p>	<p>Description</p> <ul style="list-style-type: none"> - Substrate: Sapphire, epitaxial layer: GaN based material - N bonding pad electrode: Au alloy - P bonding pad electrode: Au alloy <p style="text-align: center;">Above drawing is not on real scale</p>
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Maximum Ratings

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward current (DC)		I_F			20	mA
Peak forward current	$t_p \leq 50 \mu\text{s}$, $t_p/T = 1/2$	I_{FM}			100	mA

Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	V_F		3.5	3.8	V
Reverse current	$V_R = 5 \text{ V}$	I_R			1	μA
Peak wavelength	$I_F = 20 \text{ mA}$	λ_p	390	395	400	nm
FWHM	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		30		nm
Radiant power*	$I_F = 20 \text{ mA}$	Φ_e	4		5	mW

*Measured on bare chip on TO-18 header

Packing

Chips on adhesive film with wire-bond side top

Art. No. 111 010



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.